

## References

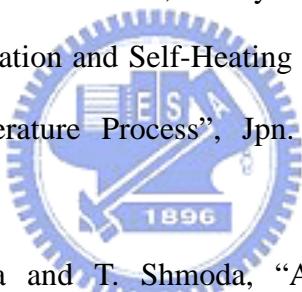
### Chapter 1

- [1.1] Y. Nakajima, "Latest Development of "System-on-Glass" Display with Low Temperature Poly-Si TFT", SID, 2004.
- [1.2] N. Kato, T. Yamada, S. Yamada, T. Nakamura, and T. Hamano, "Degradation mechanism of polysilicon TFT's under D.C. stress," IEDM Tech. Dig., pp. 677–680, 1992.
- [1.3] S. Inoue, and H. Ohshima, "New degradation phenomenon in wide channel poly-Si TFTs fabricated by low temperature process", IEDM Tech. Dig., pp. 781–784, 1996.
- [1.4] Y. Mishima, K. Yoshino, M. Takei, and N. Sasaki, "Characteristics of low-temperature poly-Si TFTs on Al/glass substrates", IEEE Trans. Electron Devices, vol. 48, pp. 1087–1091, 2001.
- [1.5] S. Inoue, H. Ohshima and T. Shimoda, "Analysis of Degradation Phenomenon Caused by Self-Heating in Low-Temperature-Processed Polycrystalline Silicon Thin Film Transistors", Jpn. J. Appl. Phys. Vol. 41, pp.6313-6319, 2002.
- [1.6] N. Kato, T. Yamada, S. Yamada, T. Nakamura and T. Hamano, "Degradation Mechanism of Polysilicon TFTs under D.C Stress", Int. Electron Device Meet. Tech. Dig., p. 677, 1992.
- [1.7] S. Inoue, H. Ohshima and T. Shimoda, "Analysis of Threshold Voltage Shift Caused by Bias Stress in low Temperature poly-Si TFTs", Int. Electron Device Meet. Tech. Dig., p. 527, 1997.
- [1.8] T. Sameshima, Y. Sunaga and A. Kohno, "Measurement of Temperature Distribution in Polycrystalline Thin Film Transistors Caused by Self-Heating", Jpn. J. Appl. Phys. 35, L308, 1996.

- [1.9] N.D. Young, A.Gill, and M.J. Edwards, “Hot carrier degradation in low temperature processed polycrystalline silicon thin film transistors”, Semiconductor Science and Technology, v 7, n 9, Sep, p 1183-1188, 1992.
- [1.10] S. Inoue and T. Shimoda, “Investigation of Relationship between Hot Carrier Degradation and Kink Effect in Low Temperature Poly-Si TFTs”, SID 1999, p.452
- [1.11] K. Okuyama, K. Kubota, T. Hashimoto, S. Ikeda, “Water-related threshold voltage instability of polysilicon TFTs” Int. Electron Device Meet. Tech. Dig., p. 527, 1993.

## Chapter 2

- [2.1] S. Inoue, S. Takenka and T. Shmoda, “Study of Degradation Phenomenon Due to a Combination if Contamination and Self-Heating in Poly-Si Thin Film Transistor Fabricated by a Low-Temperature Process”, Jpn. J. Appl. Phys. Vol. 42, pp. 4213-4217, 2003.



- [2.2] S. Inoue, M. Kimura and T. Shmoda, “Analysis and Classification of Degradation Phenomena in polycrystalline-Silicon Thin Film Transistors Fabricated by a low-Temperature Process Using Emission Light Microscopy”, Jpn. J. Appl. Phys. Vol. 42, pp. 1168-1172, 2003.

- [2.3] S. Inoue, H. Ohshima and T. Shmoda, “Analysis of Degradation Phenomenon Caused by Self-Heating in low-Temperature-Processed Polycrystalline Silicon Thin Film Transistors”, Jpn. J. Appl. Phys., Vol. 41 , pp. 6313-6319, 2002.

## Chapter 4

- [4.1] A. G. Lewis, I.-W. Wu, M. Hack, A. Chiang, and R. H. Bruce, “Degradation of polysilicon TFTs during dynamic stress”, IEDM Tech. Dig., pp. 575–578, 1991.
- [4.2] M. Hack, A. G. Lewis, and I.-W. Wu, “Physical models for degradation effects in

polysilicon thin-film transistors”, IEEE Trans. Electron Devices, vol. 40, pp. 890–897, May. 1993.

[4.3] W.-Y. Guo, C.-Y. Meng, A. Shih and Y.M. Tsai, “Reliability of low temperature poly-Si thin film transistor”, Soc. Inform. Displ. Tech. Dig., pp. 1–4, 2003.

[4.4] K. M. Chang, Y. H. Chung, and G. M. Lin, “Anomalous variation of off-state leakage current in poly-Si TFT under static stress”, IEEE Electron Device Lett., vol. 23, pp. 255–257, May. 2002.

